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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/693,847
		Filing Date	10/20/03
		First Named Inventor	August et al.
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Sheet 2 of 2	Attorney Docket Number	84,355	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS); title of the article (when appropriate); title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	7
DR		MCGREGOR et al, "Self-Biased Boron-10 Coated High-Purity Epitaxial GaAs Thermal Neutron Detector" IEEE transactions on nuclear science, vol. 47, no., August 2000	
DR		MCGREGOR et al, "Recent Results From Thin-Film-Coated Semiconductor Neutron Detectors" X-Ray and Gamma-Ray Detector and Application IV, vol. 4784 (2002).	
DR		HAQUE et al, "Neutron dosimetry employing soft errors in dynamic random access memories" Phys. Med. Biol., 1989 vol. 34, no 9, 1195-1202 Printed in the UK	
DR		PHILLIPS et al, "Feasibility of a Neutron Detector-Dosemeter Based on Single-Event Upsets in Dynamic Random-Access Memories" Radiation Protection Dosimetry vol. 101, nos. 1-4, pp. 129-132 (2002) Nuclear Technology Publishing	
DR		ROBERTSON et al, "A class of boron-rich solid-state neutron detectors" Applied Physics Letters volume 80, number 19, 13 May 2002	
DR		GUARINI et al, "Electrical Integrity of State-of-the-Art 0.13 um SOI-CMOS Devices and Circuits Transferred for Three-Dimensional (3D) Integrated Circuit (IC) Fabrication" 0-7803-7462-2/02 2002 IEEE	
DR		ARITA et al, "Experimental Investigation of Thermal Neutron-Induced Single Event Upset in Static Random Access Memories" Jpn. J. Appl. Phys Vol. 40 (2001) pp. L151-L153 Part 2, No. 2B, 15 February 2001	
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DR		LUND et al, "Neutron Dosimeter Using a Dynamic Random Access Memory as a Sensor" IEEE Transactions on Nuclear Science, Vol. 33, No. 1, February 1996	
DR		PETERSEN et al, "Calculation of Cosmic-Ray Induced Soft Upsets and Scaling in VLSI Devices*" IEEE Transaction on Nuclear Science, Vol. NS-29, No. 6, December 1982	
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Examiner Signature		Date Considered	10/6/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

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